

Title of Change:		Update Notice of FPCN20937X - Reliability Data update of NTMFS4C05NT1G.				
Proposed first ship date:		17 December 2015				
Contact information:		Contact your local ON Semiconductor Sales Office or <mohdhezri.abubakar@onsemi.com></mohdhezri.abubakar@onsemi.com>				
Samples:		Contact your local ON Semiconductor Sales Office or <michael.mooney@onsemi.com></michael.mooney@onsemi.com>				
Additional Reliability Data:		Contact your local ON Semiconductor Sales Office or <don.knudsen@onsemi.com></don.knudsen@onsemi.com>				
Type of notification:		ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <pcn.support@onsemi.com>.</pcn.support@onsemi.com>				
Change category:		Wafer Fab Change Assembly Change Test Change Other				
Change Sub-Category(s): Manufacturing Site Change/ Manufacturing Process Chan			<ul> <li>Datasheet/Product Doc change</li> <li>Shipping/Packaging/Marking</li> <li>Other:</li> </ul>			
Sites Affec		d: ☐ not applicable ☐ ON Semiconductor site(s) : ⊠ External Foundry/Subcon site(s) Aizu Fujitsu Semiconductor Manufacturing, Japan		e(s)		
Description a This Update No NTMFS4C05NT	otification is issued	to customers to provide updated Reliability data of	f HTRB and HTGB at 10	008 hrs from the qualif	ication vehicle	
This Update No NTMFS4C05NT FPCN20937X w Aizu Fujitsu Se sourced from in Reliability Da	otification is issued 11G. was issued to custor emiconductor Manue its current ON Semic ata Summary: TMFS4C05NT1G	to customers to provide updated Reliability data of mers on the qualification of the additional wafer fa acturing (AFSM) located in Aizu, Japan. At the exp onductor wafer fab in Gresham and AFSM.	abrication capacity of 3	30V Trench (T6) MOSF	ET technology i	
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## **Electrical Characteristic Summary:**

There is no change in electrical parametric performance. Characterization data is available upon request.



Part Number	Qualification Vehicle
NTMFS4C05NT1G	NTMFS4C05NT1G
NTMFS4C05NT3G	NTMFS4C05NT1G
NTMFS4C06NT1G	NTMFS4C05NT1G
NTMFS4C08NT1G	NTMFS4C05NT1G
NTMFS4C08NT3G	NTMFS4C05NT1G
NTMFS4C09NT1G	NTMFS4C05NT1G
NTMFS4C09NT3G	NTMFS4C05NT1G
NTMFS4C10NT1G	NTMFS4C05NT1G
NTMFS4C13NT1G	NTMFS4C05NT1G
NTMFS4C13NT3G	NTMFS4C05NT1G
NTMFS4C35NT1G	NTMFS4C05NT1G
NTMF54C35NT3G	NTMFS4C05NT1G